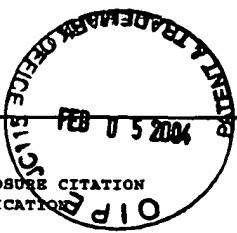


FORM PTO-1449 (Modified) INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)							
							
				Docket No. P0147US2-7		Application Number 10/665,595	
				Applicant THIBEAULT, BRIAN et al.			
				Filing Date September 17, 2003		Group Art Unit	

## U.S. PATENT DOCUMENTS

Examiner Initial	Document Number								Date	Name	Class	Subclass	Filing Date If Appropriate
J. T.	5 7 7 9 9 2 4								07/1998	KRAMES et al.	216	24	
J.	3 9 5 4 5 3 4								05/1976	SCIPRES et al.	156	7	
J.	5 7 9 3 0 6 2								08/1998	KISH et al.	257	98	
J.	5 3 5 9 2 0 8								10/1994	KATSUKI et al.	257	82	
J.	5 4 1 4 2 8 1								05/1995	WATABE et al.	257	95	
J.	5 4 9 1 3 5 0								02/1996	UNNO et al.	257	99	
J.	5 5 2 8 0 5 7								06/1996	YANAGASE et al	257	96	
J.	5 5 7 1 1 5								09/1996	SHAKUDA	257	81	
J.	6 4 1 0 9 4 2								06/2002	THIBEAULT et al	257	88	
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J.	5 7 4 4 8 2 8								04/1998	NOZAKI et al.	257	94	

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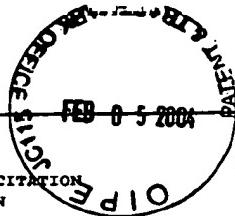
	Document Number								Date	Country	Class	Subclass	Translation		
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J. T.	WO	99	5	3	5	7	8	10-21-99	PCT					X	
J. T.	11	2	7	4	5	6	8	10-08-99	JAPANESE						X
J. T.	WO	01	41	22	5	A	2	06-07-01	PCT					X	
J. T.	EP	09	77	27	7	A	1	11-13-98	EUROPE					X	
J. T.	DE	26	33	19	1	A	1	07-23-76	GERMAN						X

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1	Egawa et al. "STIMULATED EMISSION CURRENT INJECTED InGaN/AlGaN SURFACE EMITTING DIODE WITH Al REFLECTOR AT ROOM TEMPERATURE", pp. 486-488, Electronics Letters, 2/29/96, Vol 32, No. 5.
	2	I. Schnitzer et al. "30% EXTERNAL QUANTUM EFFICIENCY FROM SURFACE TEXTURED, THIN-FILM LIGHT-EMITTING DIODES", 1993 American Institute of Physics, pp. 2174-2176.

Examiner	J. T. - Nod	Date Considered	7/22/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

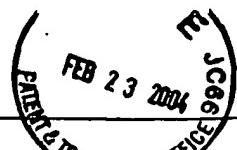


FORM PTO-1449 (Modified)	Docket No. P0147US2-7	Application Number 10/665,595
INFORMATION DISCLOSURE CITATION IN AN APPLICATION	Applicant THIBEAULT, BRIAN et al.	
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FORM PTO-1449 (Modified)

**INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION**

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Docket No.  
P0147U82

Application Number  
10/665,595

**Applicant**  
THIBEAULT, BRIAN et al.

Filing Date  
9/17/2003

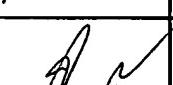
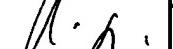
## **Unit**

**U.S. PATENT DOCUMENTS**

## FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	<p>1 A. KOCK AND E. GORNICK, <u>STRONGLY DIRECTIONAL EMISSION FROM AlGaAs/GaAs LIGHT-EMITTING DIODES</u>, Applied Physics Letters 57, pp. 2327-2329 (1990)</p>
	<p>2 KRAMES et al., <u>HIGH POWER TRUNCATED INVERTED PYRAMID (Al<sub>x</sub>Ga<sub>1-x</sub>)<sub>y</sub>In<sub>z</sub>P/GaP LIGHT-EMITTING DIODES EXHIBITING &gt;50% EXTERNAL QUANTUM EFFICIENCY</u>, Applied Physics Letters 75, pp. 2365-2367 (1999)</p>
	<p>3 SCHNITZER et al., <u>ULTRAHIGH SPONTANEOUS EMISSION QUANTUM EFFICIENCY, 99.7% INTERNALLY AND 72% EXTERNALLY, FROM AlGaAs/GaAs/AlGaAs DOUBLE HETEROSTRUCTURES</u>, Applied Physics Letters 62, pp. 131-133 (1993)</p>